

BD142

NPN SILICON TRANSISTOR POWER LINERAR AND SWITCHING APPLICATIONS

LF Large Signal Power Amplification
Low Saturation Voltage
High Dissipation Rating
Intended for a wide variety of intermediate-power applications.
It is especially suited for use in audio and inverter circuits at 12 volts.
Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V _{CEO}	Collector-Emitter Voltage		45	V
V _{CBO}	Collector-Emitter Voltage		50	V
V_{EBO}	Emitter-Base Voltage		7	V
V _{CEX}	Collector-Emitter Voltage V _{BE} =-1.5	V	50	V
Ic	Collector Current		15	Α
I _B	Base Current —		7	Α
P _T	Power Dissipation $@ T_C = 2$	5°	117	Watts
TJ	Junction Temperature		-65 to +200	°C
Ts	Storage Temperature		03 10 +200	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-C}	Thermal Resistance, Junction to Case	ase 1.5 °C/W	

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Тур	Max	Unit
V _{CEO(BR)}	Collector-Emitter Breakdown Voltage (*)	I _C =200 mA, I _B =0	45			V
V _{CEX(BR)}	Collector-Emitter Breakdown Voltage (*)	I _C =100 mA, V _{BE} =-1.5 V	50			V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage (*)	I _C =4 A, I _B =0.4 A	-	-	1.1	V
I _{CEX}	Collector-Emitter Cutoff Current	$V_{CE} = 40 \text{ V}, V_{BE} = -1.5 \text{ V}$	1	-	2	mA
I _{EBO}	Emitter-Base Cutoff Current	V _{EB} =7 V	ı	-	1	mA
V_{BE}	Base-Emitter Voltage (*)	I _C =4.0 A, V _{CE} =4.0V	1	-	1.5	V
I _{S/B}	Second Breakdown collector current	t=1s, V _{CE} =39 V	3	-	-	Α
h _{FE}	Static Forward Current Transfer Ratio (*)	V_{CE} =4.0 V, I_{C} =4.0 A	12.5	-	160	
		V_{CE} =4.0 V, I_{C} =0.5 A	20	-	-	_

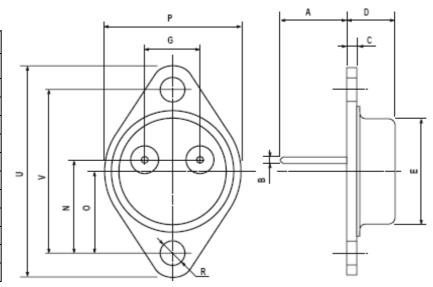
^(*) Pulse Width \approx 300 μ s, Duty Cycle \angle 2.0%



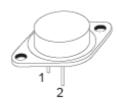
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)			
	min	max	
А	11	13.10	
В	0.97	1.15	
С	1.5	1.65	
D	8.32	8.92	
F	19	20	
G	10.70	11.1	
N	16.50	17.20	
Р	25	26	
R	4	4.09	
U	38.50	39.30	
V	30	30.30	



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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